Electric dipole spin resonance induced by hole k-linear Rashba effect in planar Ge

Yang Liu,1,2 Jia-Xin Xiong,1,2 Zhi Wang,1 Wen-Long Ma,1 Shan Guan,1,* Shu-Shen Li,1,2 and Jun-Wei Luo1,2,3,

1State Key Laboratory of Superlattices and Microstructures, Institute of Semiconductors, Chinese Academy of Sciences, Beijing 100083, China
2Center of Materials Science and Optoelectronics Engineering, University of Chinese Academy of Sciences, Beijing 100049, China
3Beijing Academy of Quantum Information Sciences, Beijing 100193, China

Hole-based qubits in planar Ge have received considerable attention due to the strong spin-orbit coupling (SOC), which is at the heart of fast and all-electric qubit control via electric dipole spin resonance (EDSR). However, most studies on hole-based EDSR have been limited to Dresselhaus SOC that is absent in Ge, which conflicts with the recent experimental observations. Here, we theoretically demonstrate that the newly-discovered hole k-linear Rashba SOC in Ge/Si quantum wells is necessarily harnessed to implement EDSR, enabling fast qubit manipulation. We investigate the Rabi frequency caused by k-linear Rashba SOC within the single-band approximation and the results are in agreement with the experiments. Moreover, by using the atomistic pseudopotential calculations, we further discuss the Rabi frequency under different gate electric fields as well as biaxial strains. Our findings thus open new perspectives for the understanding of EDSR in planar Ge, which is vitally important toward future semiconducting quantum computation.

Hole spin states in Ge quantum dot have recently emerged as a powerful platform for quantum computing [1]. Besides the purified host crystal containing only isotopes with zero nuclear spins [2] and p-symmetry of valence band [3], which guarantee long coherence times, the most important advantage of hole in Ge is its strong spin-orbit coupling (SOC) [4]. SOC utilized in Electric dipole spin resonance (EDSR) plays a vital role in fast and all-electrical manipulation of the qubit [3, 5, 6]. The demonstration of coherent control is implemented by Rabi oscillations and the Rabi frequency reflects the speed of the control [3, 5, 7].

The strong and tunable direct Rashba spin-orbit interaction (DRSOI), which was discovered by Luo et al. [8] and Kloeffel et al. [9] independently, enables ultrafast single-qubit gates in Ge/Si nanowires via EDSR [10]. This SOC was confirmed by experiment [11] and enables an electrical control on the g factor [12, 13]. Another widely studied platform is Ge hut wires [14–16], which has achieved a record Rabi frequency of 540 MHz for semiconductor spin qubits [17]. Furthermore, in the past few years, the gate-defined quantum dots in planar Ge have realized single-qubit logic [18], fast two-qubit logic in double quantum dots [19], singlet-triplet encoding [20], and a four-qubit quantum processor [21]. Planar Ge is also a promising platform for hybrid superconductor-semiconductor devices [22, 23]. The Rabi frequency of around 100 MHz measured in these experiments indicated the existence of a strong SOC in planar Ge [19]. However, there are many kinds of SOC for two-dimensional hole gases (2DHGs) due to the complex valence-band structure, and it remains speculative which one leads to EDSR in planar Ge [24].

The implementation of EDSR depends on the energy level coupling caused by SOC [3, 5, 25]. We consider a quantum dot in planar Ge, which is exposed to a static magnetic field $B$ and an ac electric field $E$, as shown schematically in Fig 1(a). The eigenstates of a quantum dot can be labeled as the product of Fock-Darwin states and spin states $|n, l, s\rangle = |n, l\rangle |s\rangle$ with princi-

![FIG. 1. A schematic illustration of the quantum dot in planar Ge and coupling of the low-energy states. (a) A heavy-hole confined in [001]-oriented Ge quantum well via a harmonic potential. The barrier layers are Si$_x$Ge$_{1-x}$ alloy. The x and y directions are along the crystallographic [100] and [010] directions respectively. The applied magnetic field $B$, which can be in-plane or out-of-plane, generates a Zeeman splitting. Rabi oscillations occur when the ac electric field $E_{ac}$ resonates with the Zeeman split. (b) The k-linear Rashba SOC (red lines) and conventional k-cubic Rashba SOC (blue lines) mix the ground states with the exited states $n = 1$ and $n = 3$, respectively. Only the k-linear Rashba SOC can support EDSR in planar Ge, which requires $\Delta n = \pm 1$ transitions (green lines).](#)
pal (azimuthal) quantum number $n$ ($l$) and $s = \pm 3/2$ (Fig 1(b)). The emergency of EDSR involves an orbital transition with $\Delta n = \pm 1$, which, however, cannot be achieved between two ground states $|0, 0, \pm 3/2\rangle$. Assisted by the SOC, the ground states $n = 0$ and the first excited states $n = 1$ with opposite pseudo-spin are coupled together to form a qubit. In this way, the ac electric field can generate a transition between the two logical states and achieve Rabi oscillations when the frequency matches the spin resonance frequency of qubit. Previous research has established that the EDSR of hole spin in planar quantum dots relies on Dresselhaus SOC [3, 26, 27], but this type of SOC is absent in Ge due to the bulk inversion symmetry. The dominant term of SOC is commonly considered to be k-cubic Rashba SOC, related to $n = \pm 3$, and therefore does not support EDSR [24], as indicated by blue lines in Fig 1(b). There are some theories to explain the origin of EDSR in planar Ge through a k-cubic Rashba SOC [28, 29], which is different from conventional Rashba SOC and relies on the small anisotropies of the valence band in Ge [30, 31]. However, the spin-splitting in the vicinity of $\Gamma$ point calculated by atomistic semi-pseudopotential method (SEPM) indicates that the k-cubic Rashba parameter is several orders of magnitude smaller than the predicted value, implying that the contribution of this term will not be as large as predicted. Moreover, the band-structure calculated by SEPM demonstrates that the spin-splitting is dominated by a k-linear term plus a minor k-cubic term, uncovering a strong and tunable k-linear Rashba SOC in 2DHGs [32].

In this Letter, based on the single-band approximation, we show that this hole k-linear Rashba SOC, which originates from a combination of heavy-hole-light-hole mixing and direct dipolar intersubband coupling to the external electric field, provides the required $\Delta n = \pm 1$ transitions (red lines in Fig 1(b)) and can support EDSR in planar Ge. The Rabi frequency is consistent with experiments and can be tuned by the gate electric field and strain. This finding suggests that the hole k-linear Rashba effect can lead to new physical phenomena for the related hole spin physics, which are always studied based on the conventional k-cubic Rashba model.

Under the single-band approximation, the effective Hamiltonian describing a HH confined in a planar QD reads

$$H_{QD} = \frac{\pi^2 + \pi^2_x}{2m} + \frac{1}{2}m_0\omega_0^2(x^2 + y^2) + \frac{1}{2}g\mu_B B \cdot \sigma + H_{SO},$$

where $\pi = P + eA$, and $A = B_z(-y, x, 0)/2$ denotes the vector potential in symmetric gauge. Here, we neglect the orbit effects induced by the in-plane components $B_x$ and $B_y$ and assume that the in-plane confinement is parabolic and circular, which can be characterized by the energy scale $\hbar\omega_0$. The in-plane heavy-hole mass $m = 0.09m_0$ is measured in experiments [19, 22]. The magnetic field induces a Zeeman splitting $E_Z = g\mu_B B$, with a spin quantization axis $n = B/B$. We should note that the $g$ factor is highly anisotropic between in-plane and out-of-plane magnetic fields. The in-plane $g$ factor observed in single-hole qubit experiments is approximately 0.3 [18], while the out-of-plane $g$ factor is 15.7 [33]. Therefore, the out-of-plane magnetic field is much smaller than the in-plane field when the same Zeeman splitting is achieved. As for spin-orbit coupling term, the calculations based on SEPM illustrates the existence of k-linear spin splitting of topmost valence sub-band HH1 and the spin-splitting is isotropic. This k-linear Rashba SOC can be described by the Hamiltonian

$$H_{SO} = \frac{\alpha}{\hbar}(\pi_x\sigma_y - \pi_y\sigma_x),$$

which is the same as Rashba term of two-dimensional electron gases (2DEGs). Here, we omit the k-cubic Rashba SOC and the term proportional to the in-plane magnetic field, which couples the ground states with $n = 3$ and $n = 2$ respectively [24]. In the framework of second quantization, it is obvious that the k-linear Rashba SOC can mix the $n = 0$ and $n = 1$ orbital states with opposite pseudo-spin and makes it possible to manipulate the qubit through an ac electric field $V(r, t) = -e\mathbf{E} \cdot \mathbf{r}$, which is the foundation of EDSR.

To quantitatively support our concept, we derive the expression of Rabi frequency $f_R$. The derivation process is the same as that for electrons [6, 34], due to the same form of SOC. Firstly, we perform a Schrieffer-Wolff transformation to diagonalize the total QD Hamiltonian $H_{QD}$. This transformation remove the spin-orbit interaction in the leading order. Then, we apply the same transformation to the total Hamiltonian including an ac electric field $H = H_{QD} + V(r, t)$ and obtain an effective Rabi-type Hamiltonian in the logical basis $\{|0\rangle, |1\rangle\}$,

$$H_{EDSR} = \frac{1}{2}g\mu_B \mathbf{B} \cdot \sigma + \frac{1}{2}\delta \mathbf{B}(t) \cdot \sigma,$$

where we omit the spin-independent part. $\delta \mathbf{B}(t)$ is the effective magnetic field induced by the combination of ac electric field and k-linear Rashba SOC [35]. The effective magnetic field $\delta \mathbf{B}(t)$ is always perpendicular to $\mathbf{B}$. Finally, we can obtain the Rabi frequency $f_R = \text{max}(|\delta \mathbf{B}(t)|)/4\hbar$. From the formula of effective magnetic field $\delta \mathbf{B}(t)$, we can find that Rabi frequency $f_R$ is strongly dependent on the directions of magnetic and ac electric fields. In particular, for an in-plane magnetic field, the Rabi frequency vanishes when the ac electric field is perpendicular to the magnetic field. Due to the large anisotropy of $g$ factor, we consider the in-plane magnetic field and the out-of-plane magnetic field separately. For the in-plane magnetic field,

$$f_R = \frac{eE_z\alpha\mu_B B}{2\hbar \left(\hbar^2\omega_0^2 - g_\|^2\mu_B^2 B^2\right)}.$$
Here, for simplicity, we set both the ac electric field and magnetic field is along $x$ direction. For the out-of-plane magnetic field,

$$f_R = \frac{eE_x \alpha g \mu_B B}{2h(\omega_+ + g \mu_B B)(\omega_- - g \mu_B B)},$$

(5)

where $\omega_\pm = \omega \pm \omega_L$, $\omega_L = eB/2m$ and $\omega = \sqrt{\omega_0^2 + \omega_L^2}$. The obtained Rabi frequency $f_R$ is proportional to the ac electric field and small magnetic field. In the following, we mainly focus on the in-plane magnetic field, which is always employed in recent experiments.

Fig 2 shows the Rabi frequency under different ac electric fields. The in-plane magnetic field and the quantum dot radius are chosen as the experimental value 1.65 T and 50 nm [36]. We choose the Rashba parameter to be 2.47 meVÅ, which corresponds to a gate electric field of 100 kV/cm. Although the hole k-linear Rashba parameter is relatively small, Rabi frequencies can reach hundreds of MHz. We can see an obvious linear relationship. The recent experiment achieved a rapid qubit control in planar Ge with the Rabi frequency exceeding 100 MHz [19] under an ac electric field of $2 \times 10^{-3}$ V/µm [36]. Under this condition, the Rabi frequency $f_R$ is calculated to be 123 MHz, which is close to the experimental value. The good agreement demonstrates that the hole k-linear Rashba SOC is the origin of EDSR in planar Ge.

The consistency between the experiment and theory reveals the role of atomistic pseudopotential calculations in quantum device design. Actually, various parameters are experimentally available to modulate the Rabi frequency. For example, the k-linear Rashba parameter can be tuned by gate electric field $E_z$, which is perpendicular to the QWs. Hence, combining the Eq (4) and SEPM, we can obtain the Rabi frequency under different gate electric fields, as shown in Fig 3. The Rabi frequency remains linear with the gate electric field up to 200 kV/cm, without a rapid transition to saturation like 1D semiconductor nanowires [37]. This difference can be understood by the expressions of hole k-linear Rashba parameter, which is obtained through quasi-degenerate perturbation theory [32],

$$\alpha_R = \frac{2e\gamma_3 C_0 U_0 E_z}{\sqrt{\Delta_0^2 + 4e^2 U_0^2 E_z^2}}.$$  

(6)

The denominator of Eq.(6) is the energy separation between HH1 and HH2 subbands: the first term ($\Delta_0$) is due to the quantum confinement effect (QCE), and the second term arises from the electric-field-induced quantum confined Stark effect (QCSE). In the [001]-oriented Ge/Si quantum wells, the QCE dominates the energy separation (i.e., $\Delta_0 \gg 2eU_0 E_z$) and $\alpha_R \approx 2e\gamma_3 C_0 U_0 E_z/\Delta_0$, which is scaled linearly as the gate electric field $E_z$. This is also true for the Rabi frequency. The saturation of the $\alpha_R$ and $f_R$ due to the strong QCSE cannot be achieved under the gate electric field commonly used in experiments.

Besides the gate electric field, the strain from barrier layers will also affect the k-linear Rashba parameter by changing the energy separation $\Delta' = \sqrt{\Delta_0^2 + 4e^2 U_0^2 E_z^2}$. In the experiments, the barrier layers of Ge quantum wells are Si$_x$Ge$_{1-x}$ alloy and thus, the quantum well is engineered to be compressively strained [38]. We explores the dependence of k-linear Rashba parameter on the biaxial strain in the [001]-oriented Ge/Si quantum wells and obtain the corresponding Rabi frequencies $f_R$, as shown in Fig 4. As the strain increases, the energy
squeezed dot is also a feasible approach to increase Rabi frequency. In addition, the use of a oriented Ge/Si quantum wells with an order of magnitude increase in Rabi frequency. Hence, \( f_R \) has a negative relationship with the compressive strain.

A key aspect of hole k-linear Rashba SOC is heavy-hole-light-hole mixing. In [001]-oriented Ge/Si quantum wells with \( D_{2d} \) symmetry, the HH-LH mixing at \( k = 0 \) originates from symmetry reduction caused by the local symmetry of the \( C_{2v} \) interface \([39, 40]\). The atomistic pseudopotential calculation presents a quantitative value for the k-linear Rashba SOC generated by this finite HH-LH coupling \([32]\). Because of the intrinsic HH-LH mixing, the k-linear Rashba SOC in [110]-oriented quantum wells is much larger than [001]-oriented quantum wells, which exceeds 120 meV\( \cdot \)\( \AA \) and is comparable to the highest values reported in narrow band-gap III-V semiconductors. We expect to achieve faster qubit manipulation in [110]-oriented Ge/Si quantum wells with [111]-oriented Ge/Si quantum wells with an order of magnitude increase in Rabi frequency. In addition, the use of a squeezed dot is also a feasible approach to increase Rabi frequency, where the DRSOI is enhanced by an asymmetric confining potential \([36]\). In this case, the quantum dot in the planar Ge is described by a wire Hamiltonian.

In conclusion, we have figured out that the hole k-linear Rashba SOC in Ge/Si quantum well enables EDSR in recent experiments. Using the single-band approximation, we obtain the expression of Rabi frequency. Although the k-linear Rashba parameter is small, the obtained Rabi frequency is of order MHz and even reaches GHz, which is consistent with the experiments. The atomistic pseudopotential method allows us to get the Rabi frequency under different gate electric fields and strains. We believe that the hole k-linear Rashba effect will bring a new perspective to semiconductor spintronics and quantum computation.

* shan.guan@semi.ac.cn
  jwluo@semi.ac.cn

[16] T. Zhang, H. Liu, F. Gao, G. Xu, K. Wang, X. Zhang,
[36] δB(t) = 2B × [Ω1(t) + n × Ω2(t)], with Ω1 = eαγ1(Ey, Ex, 0) and Ω2 = eαγ2(−Ex, −Ey, 0), γ1 = (E2Z − ℏω0)2(E2 + −E2Z)(E2 − −E2Z), γ2 = ℏωc(E2Z)(E2 + −E2Z)(E2 − −E2Z).